

#### **Alcatel Micro Machining Systems**



# **Enabling DRIE processes for high**potential MEMS products

Michel PUECH October 12th 2006



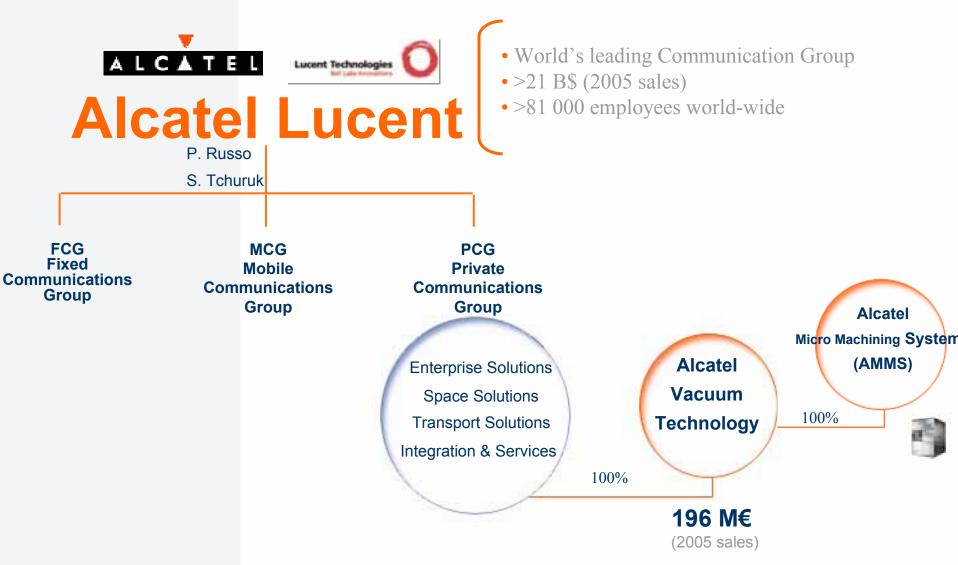
#### **Outline**

- Introduction
  - who we are ?
  - market and applications
- DRIE for MEMS
  - Bosch Process
  - High etch rate
  - Super High Aspect Ratio
  - Aspect Ratio Dependent Etching
- Conclusion
  - from MEMS to smart Systems integration





# Part of a worldwide leader, high technology, Multinational corporation





#### AMMS Global network

... Market proximity, competence & optimized cost

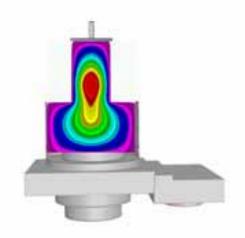


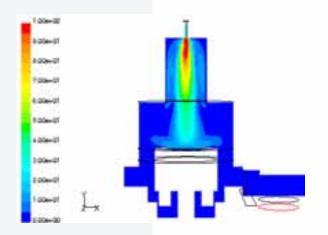


## AMMS HDP Technologies

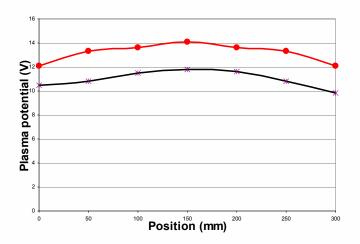
#### AMMS Patented Plasma source

- De-coupled plasma process chamber
- Low temperature plasma
- High uniformity on large diameter
- Design for uniform and high gas flow rate





#### Plasma potential mapping

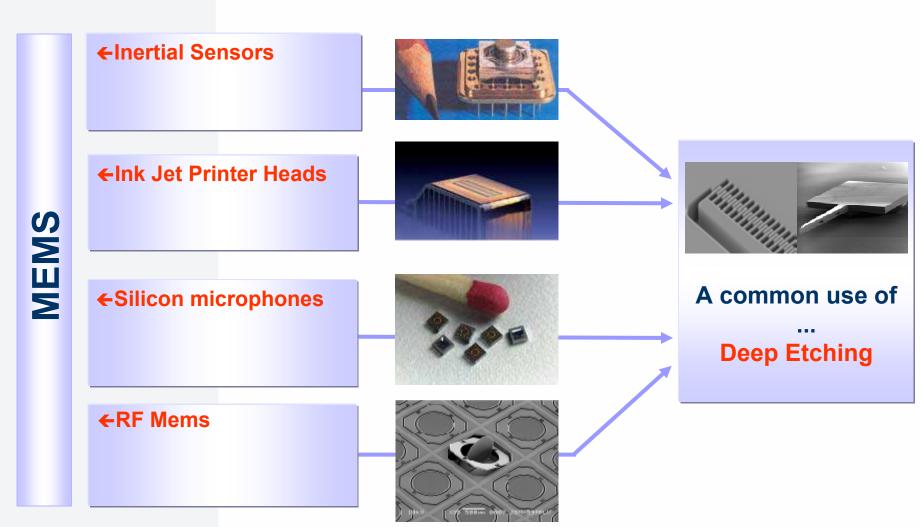




## Markets and Technologies

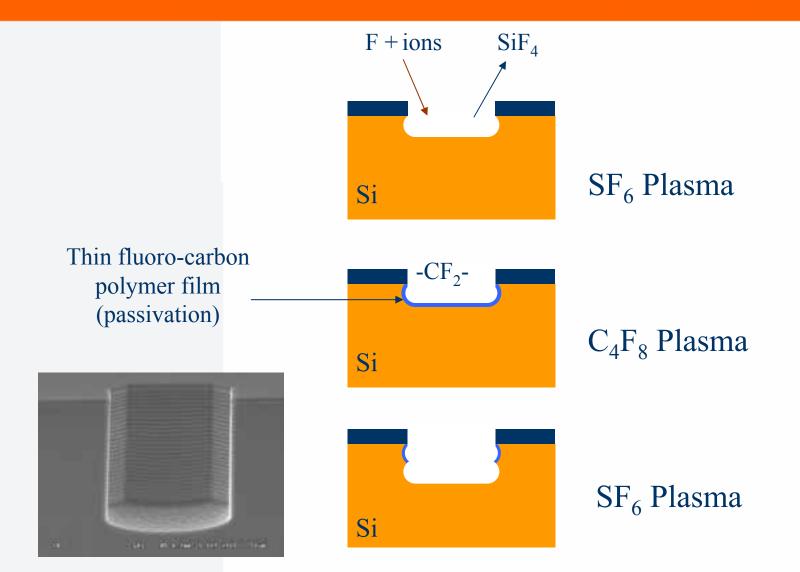
... MEMS Market

Deep Etching Technique is Key to address the 3<sup>rd</sup> Dimension





#### **Bosch Process**

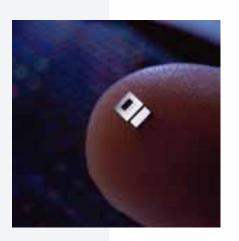


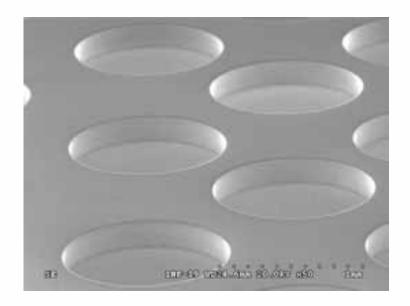


#### MEMS: Silicon microphones



Big performance from a small, low-cost chip is the claim to fame of this multimicrophone MEMS IC with an orbicard amplifier. Produced by Austria, it heraids the next technological revolution in accustics for the heading impaired and for cell phones.

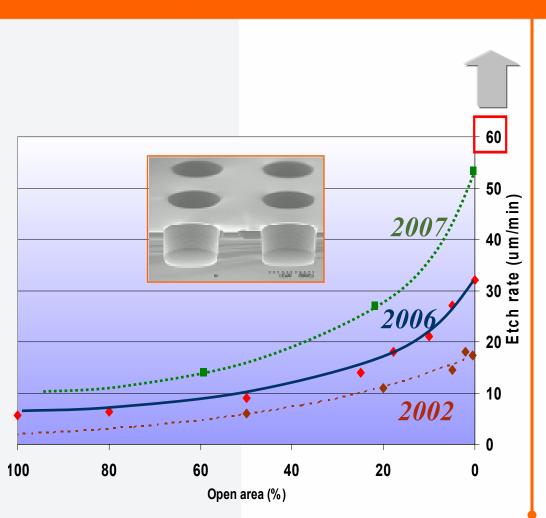




- Accurate depth control
- Etching of large silicon surfaces
- High uniformity at high etch rate (>8µm/mn)



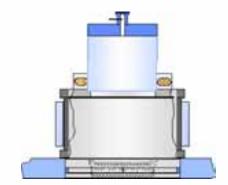
#### Technology leadership



Being first to push Bosch process limits and bring into market cost effective high etch rate capabilities

(I-Speeder project 2001- cooperation with Robert Bosch)

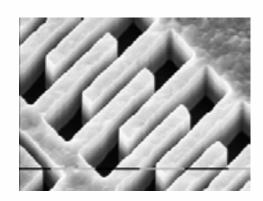
- Introducing MEMS specific handling and clamping solutions
- The only OEM providing both Cryogenic and room temperature etching capabilities

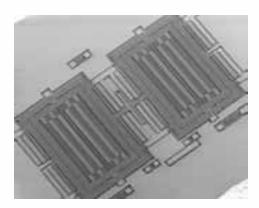




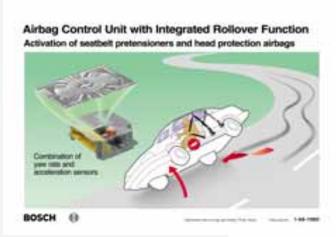
#### **MEMS:** Inertial sensors







Coutersy of Robert Bosch

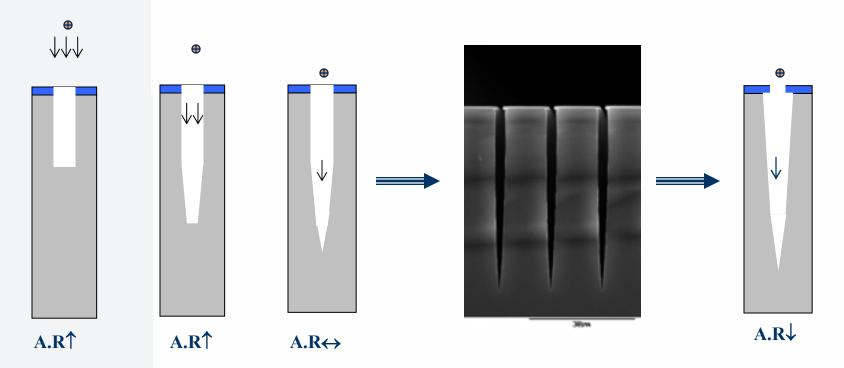


- Vertical profile control
- High uniformity at high etch rate
- Higher Aspect Ratio
- Etching of large and narrow features with controlled ARDE





Improper removal of bottom polymer layer

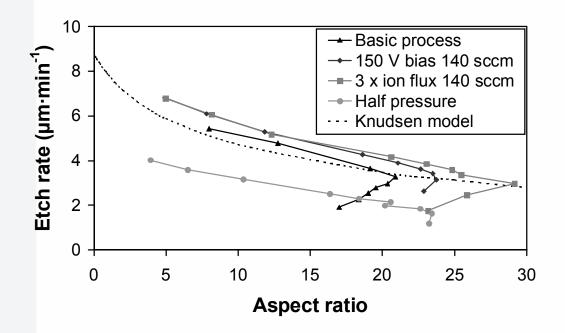


With standard "Bosch" process Aspect Ratio limited at 20



## Standard ways of improvement

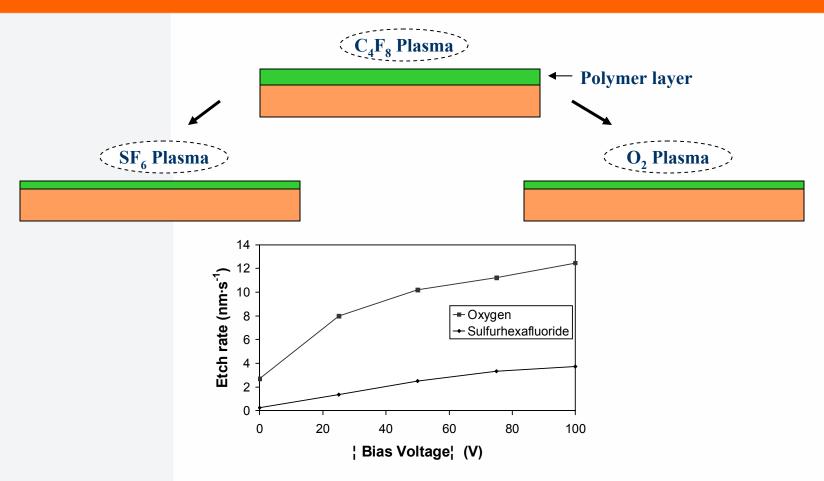
Decrease process pressure, increase ion energy, ion flux



- Improved Aspect Ratio up to 30 but!
- Decrease of etch rate and/or selectivity



### New way of improvement



- O<sub>2</sub> Plasma removes polymer 5 time faster than SF<sub>6</sub>!!
- Polymer/Si]SF6 << 1 while [Polymer/Si]O2 >>1



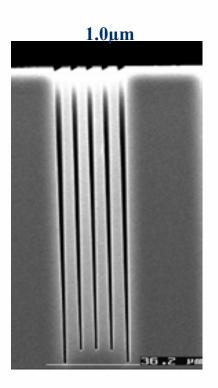


#### New Alcatel process with optimal polymer removal





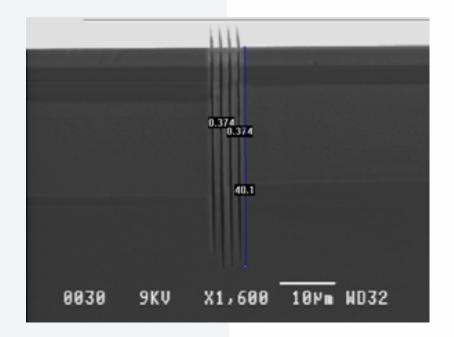




Aspect Ratio > 60



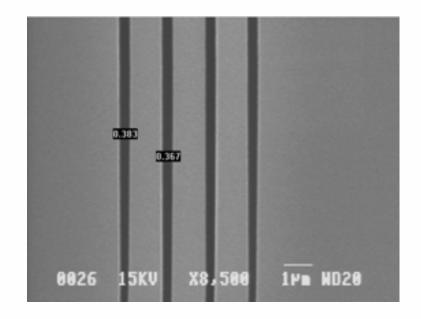
# Super High Aspect Ratio Process



Trench Width: 0.374 µm

Depth: 40.1 µm

**Aspect Ratio >100** 



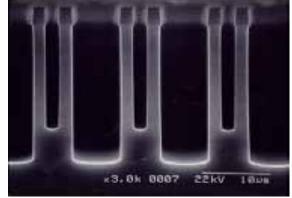
By courtesy of ESIEE - Paris

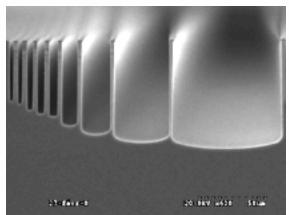


## ARDE in DRIE Silicon Etching

# ARDE is the physical effect where the etch rate decreases when increasing the aspect ratio.

- Structures with different dimensions have non uniform etch rate.
- Complex devices cannot be made
  - Substrate with etch stop layer ⇒SOI wafers.
  - High over etch time to complete the etching of the narrow structures.







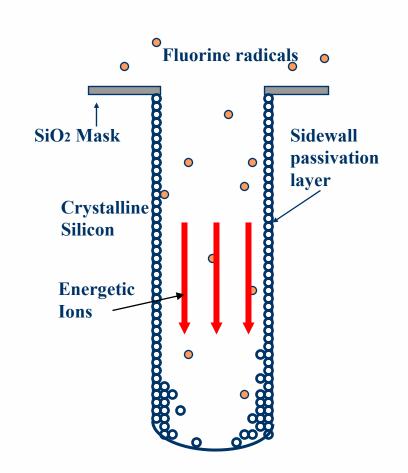


#### > Radical's Depletion

Knudsen transport

#### Ion Depletion

- Side wall scattering
- Electronic deflection
- Angular distribution

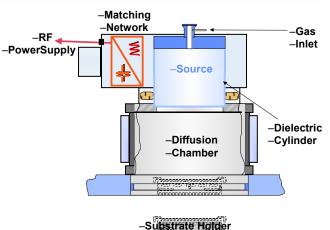




#### Experimental Setup

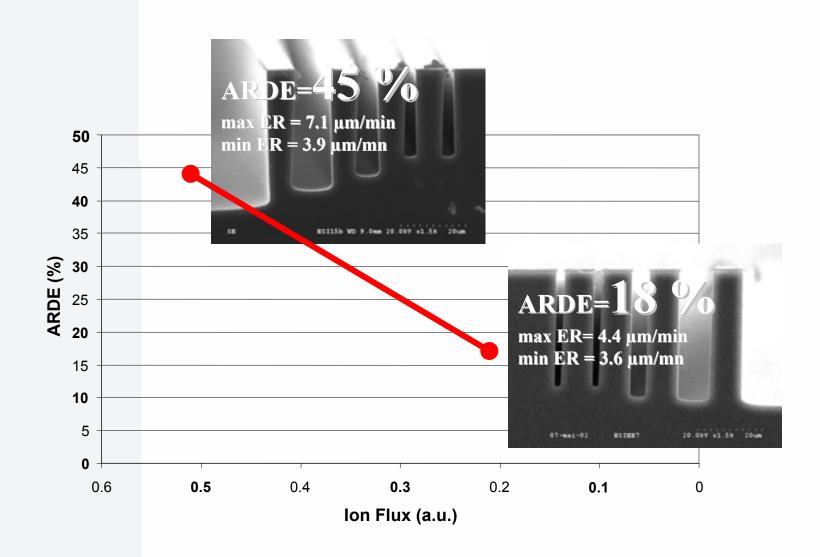
- AMS 200 "I-Speeder"
- Alcatel test wafers : trench widths
   200/10 μm, 20% Si exposed area
- "Bosch" Process:Time multiplexed etch/passivation
- 'ARDE" = (ER max ER min)/ER max





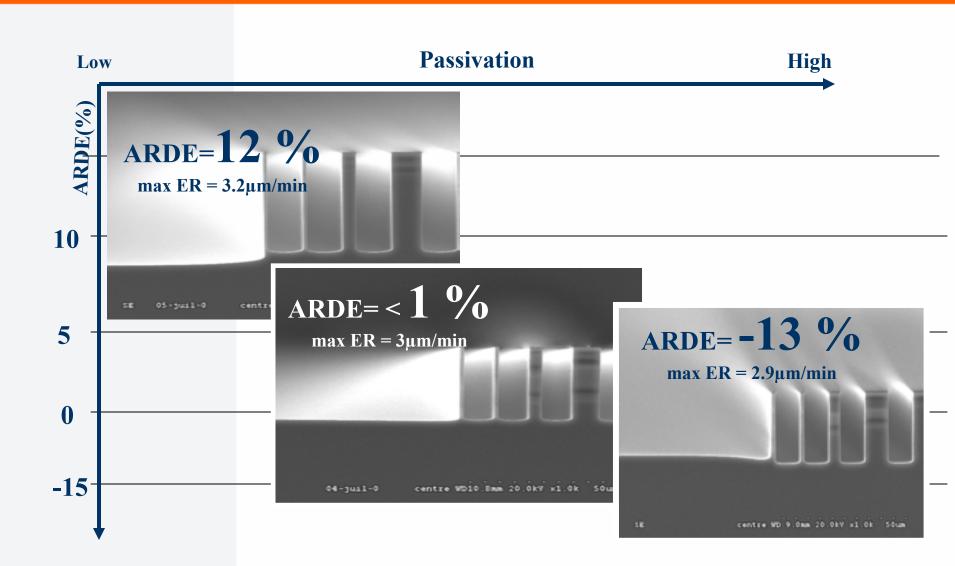


#### Ion Flux Effect





#### **Passivation Control**





#### Conclusion

... from MEMS to Smart System Integration

#### **Semiconductor**

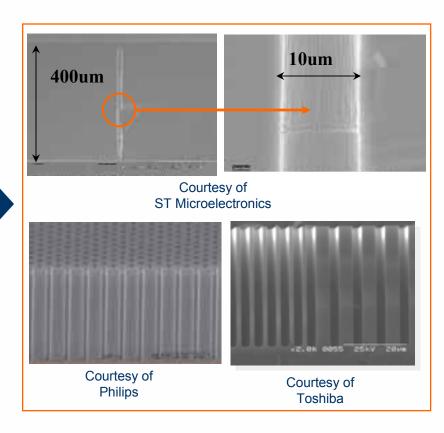


#### **Manufacturing Tools 3D**

- Deep Etching
- Lithography
- Bonding, ...



# 3D SC •3D Chips •Wafer Level Packaging





#### **Alcatel Micro Machining Systems**



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